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(54) Title: METHOD FOR PRODUCING HYBRID COMPONENTS

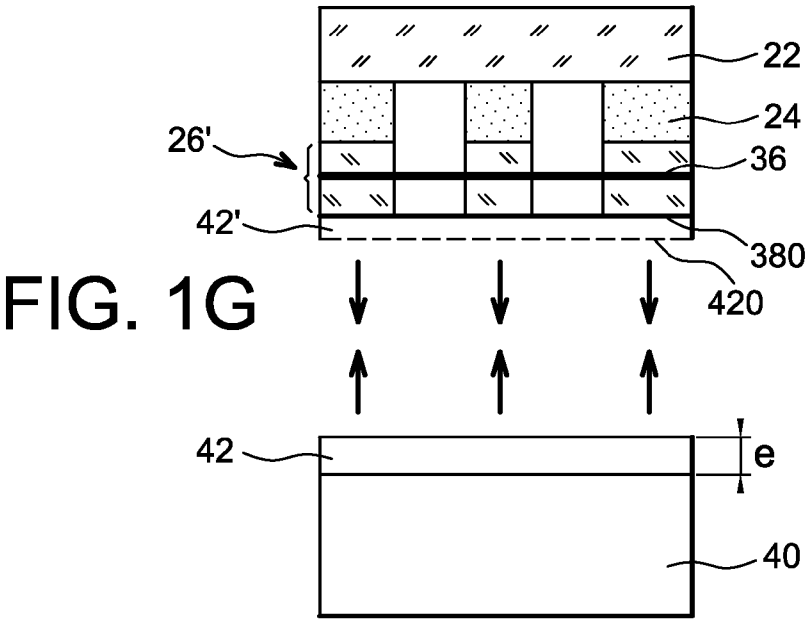


FIG. 1G

(57) Abstract: The invention concerns a method for producing a hybrid substrate, comprising a support substrate (40), a continuous buried insulator layer (42) and, on this layer, a hybrid layer (26) comprising alternating zones of a first material (26) and at least one second material (32), wherein these two materials are different by their nature and/or their crystallographic characteristics, said method comprising: - the formation of a hybrid layer (26), comprising alternating zones of first and second materials, on a homogeneous substrate (22), - the assembly of this hybrid layer, the continuous insulator layer (42) and the support substrate (40), - the elimination of a part at least of the homogeneous substrate (40), before or after the assembly step.

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